/ Descriptions

TO-220 ṂṂ Ḅ N ʂ MOS ʃ ѽ Ẓ ㄱ N-CHANNEL MOSFET in a TO-220 Plastic Package.

/ Features

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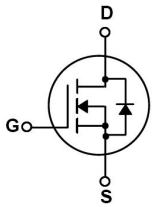
Fast switching, low on resistance, low gate charge, low reverse transfer capacitances.

/ Applications

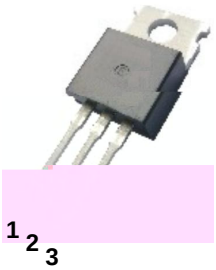
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Used in various power switching circuit for system miniaturization and higher efficiency.

/ Equivalent Circuit



/ Pinning



PIN1 χ G PIN 2 χ D PIN 3 χ S

/ h_{FE} Classifications & Marking

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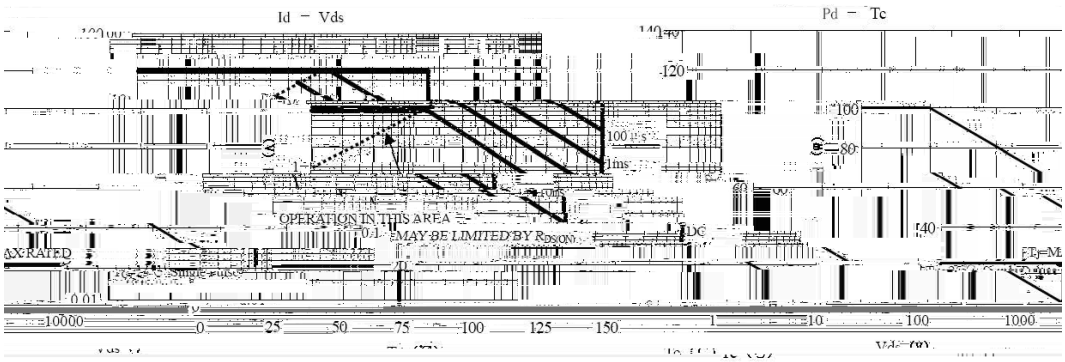
/ Absolute Maximum Ratings(Ta=25)

v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Drain-Source Voltage	V_{DSS}	700	V
Drain Current	I_D(Tc=25)	6.0	A
Drain Current	I_D(Tc=100)	3.6	A
Drain Current - Pulsed	I_{DM}	24	A
Gate-Source Voltage	V_{GS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	185	mJ
Repetitive Avalanche Energy	E_{AR}	20	mJ
Avalanche Current	I_{AR}	3.3	A
Power Dissipation	P_D(Tc=25)	100	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	
Junction-to-Case	R_{dJC}	1.25	/W
Junction-to-Ambient	R_{dJA}	62	/W

/ Electrical Characteristics(Ta=25)

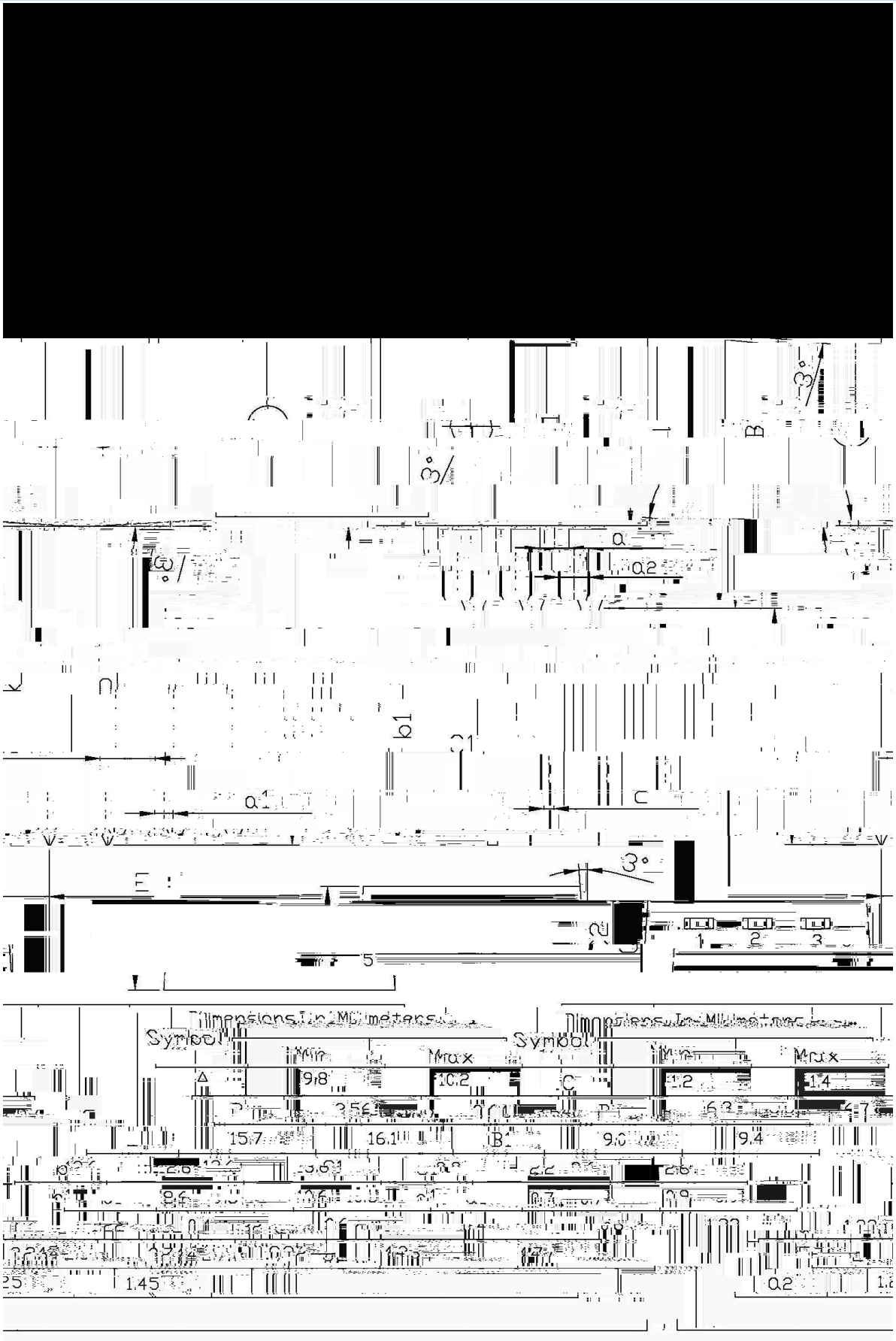
v ̈Ω Parameter	ϒ N Symbol	Ш :† ţ Test Conditions	ѡ ņ Ö Min	Ɛ ʒ Ö Typ	ѡ ᶻ Ö Max	D Ч Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250εA	700			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=700V V_{GS}=0V			1	εA
		V_{DS}=560V T_a=125			100	εA
Gate-Body Leakage Current, Forward	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±10	εA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250εA	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V I_D=3.0A		1.35	1.6	q
Forward Transconductance	g_{FS}	V_{DS}=15V I_D=3.0A		5.0		S
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=6.0A			1.5	V
Input Capacitance	C_{iss}	V_{DS}=25V V_{GS}=0V f=1.0MHz		938		pF
Output Capacitance	C_{oss}			87.8		pF
Reverse Transfer Capacitance	C_{rss}			8.2		pF
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=350V I_D=6.0A R_G=25q V_{GS}=10V		14.7		ns
Turn-On Rise Time	t_r			26		ns
Turn-Off Delay Time	$t_{d(off)}$			68.4		ns
Turn-Off Fall Time	t_f			34.6		ns

/ Electrical Characteristic Curve

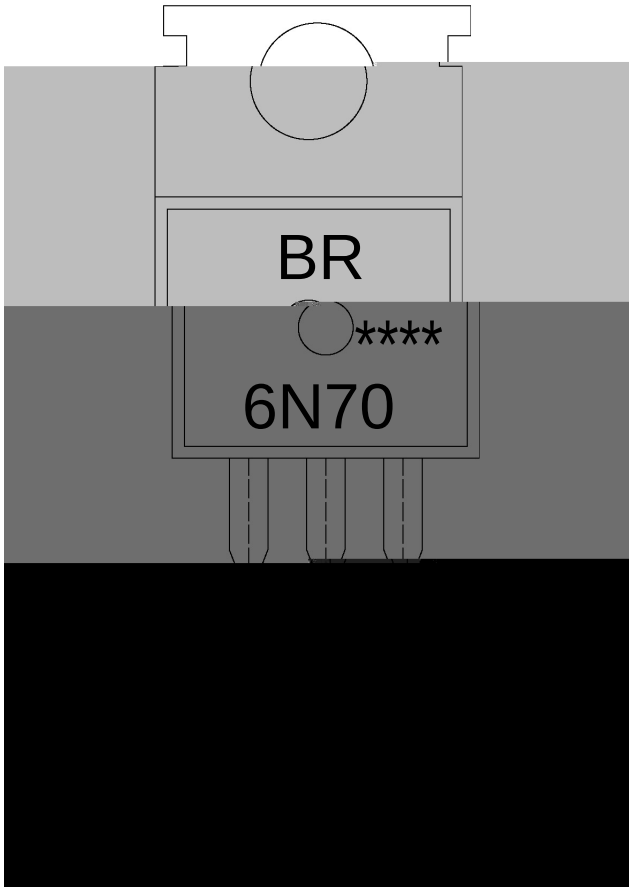




/ Package Dimensions



/ Marking Instructions

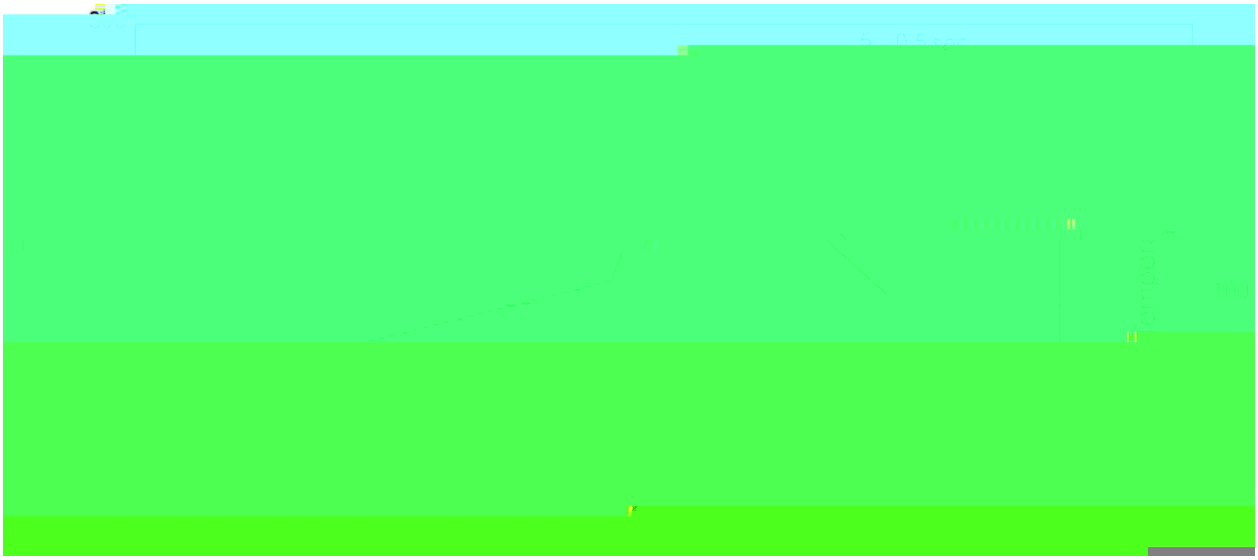


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BR χ	ᵻᵿ ϛ ᴺ Ղ
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Note:

BR:	Company Code
6N70:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı `H ڑ `Y ﾊ ㎛ 5 ° 0.5sec;

3 ì ˙ ｲ ˛ ɔ ﻉ ỷ ㎛ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ł `H ڑ χ 10 ° 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

¨Ω ţ ｲ Ł / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195